L Number	Hits	Search Text	DB	Time stamp
1	38	ueda near2 tetsuzo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/22 14:17
–	24	iii near2 nitride and (both adj side) same deposit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:20
–	78	iii near2 nitride and (top same bottom) same deposit$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:25
–	96	double near2 sid$2 near2 (epitax$4 or deposit$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:27
–	4	(double near2 sid$2 near2 (epitax$4 or deposit$4)) and 117/$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:37
–	0	5356831.pn. and remov$3 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:40
–	2	5356831.pn. and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/31 10:40
–	353	olsen.in. and bow$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 18:08
–	2	olsen.in. and bow$3 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 18:09
–	1280	bow$3 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/09 18:09
–	38	bow$3 near10 wafer same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 11:05
–	96	bow$3 near10 wafer near10 flat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 13:47
–	687	deposit$ near15 wafer near10 flat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 13:50
–	70	deposit$ near15 wafer near10 (flatten or flattening or flattens)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 13:50

C:\APPS\east\workspaces\09904131.wsp

–	3	5562770.URPN.	USPAT	2004/02/10 13:53
–	12	("3458369" | "3808674" | "3821033" | "3997368" | "4079506" | "4159214" | "4415373" | "4631804" | "4805071" | "4830984" | "5158907" | "5319570").PN.	USPAT	2004/02/10 13:54
–	225	direct near5 heat$4 and 117/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:32
–	66	direct near5 heat$4 and 117/$.ccls. and (chemical adj vapor adj deposition or cvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:36
–	1911	without near4 heat near2 sink	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:36
–	77	(without near4 heat near2 sink) and (cvd or chemical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:38
–	6	((without near4 heat near2 sink) and (cvd or chemical adj vapor adj deposition)) and 117/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:37
–	5	(without near4 heat near2 sink) same (direct$4 near2 heat$4) and (cvd or chemical adj vapor adj deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:38